

Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.356US1	Serial No. 08/902,133
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: July 29, 1997	Group: 2815

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
						If Appropriate
<i>Omew</i>	4,460,670	07/01/1984	Ogawa, et al.	430	51.7 577	
<i>Omew</i>	4,657,699	04/01/1987	Nair	252	513	
<i>Omew</i>	4,738,729	04/01/1998	Yoshida, et al.	136	258	
<i>Omew</i>	5,145,741	09/01/1992	Quick	428	402	
<i>Omew</i>	5,604,357	02/18/1997	Hori, T.	257	24	07/11/95
<i>Omew</i>	5,801,401	09/01/1998	Forbes, L.	257	77	

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<i>Renew</i>	5,714,766	02/03/1998	Chen, et al.	257	20	09/29/95
<i>Renew</i>	5,754,477	05/19/1998	Forbes	365	185.33	01/29/97

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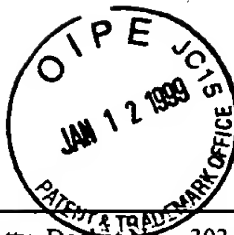
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<i>VMW</i>	5,623,442	04/22/1997	Gotou, H., et al.	365	185.08	06/08/94
<i>VMW</i>	5,786,250	07/28/1998	Wu, Z., et al.	438	254	03/14/97

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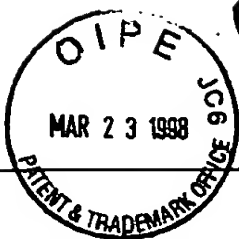
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<i>Vmur</i>	5,111,430	05/05/1992	Morie	365	185 185.24	06/21/90
<i>Vmur</i>	5,260,593	11/09/1993	Lee	257	316	12/10/91
<i>Vmur</i>	5,293,560	03/08/1994	Harari	365	185 185.03	11/03/92
<i>Vmur</i>	5,369,040	11/29/1994	Halvis, et al.	437 438	3 22	04/12/93
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<i>Vmur</i>	5,465,249	11/07/1995	Cooper, et al.	365	149	11/26/91
<i>Vmur</i>	5,477,485	12/19/1995	Bergemont, et al.	365	185.24	02/22/95
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<i>Vmur</i>	5,670,790	09/23/1997	Katon, et al.	257	14	09/19/96

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<i>Vmur</i>	6-302828	10/28/1994	Japan	H01L	29/788	
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Examiner

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Date Considered

3/3/99

*Substitute Disclosure Statement Form (PTO-1449)

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